



Reliability Qualification Report

for

DDR SDRAM with Pb/Halogen Free

(32Mx16, 45nm SDRAM AS4C32M16D1-5BCN)

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Reliability Qualification Report for
AS4C32M16D1-5BCN
(32M x 16 DDR SDRAM with Pb/Halogen Free)

0. RELIABILITY TEST SUMMARY

| Test Item | Test Condition | Pass Criteria | Test Result |
|-----------|--|------------------------------|-----------------------------------|
| EFR | 1.2*Vint, 125°C, 12Hrs | 0 - 1 (Year) ≤ 1000 (DPM) | 0/1000 0 DPM (PASS) |
| OLT | 1.1*Vint, 125°C, 1000Hrs | 1 - 10 (Year) | 0/231 11 FIT (PASS) |
| | | ≤ 50 (FIT) | MTBF= 91 x 10 ⁶ Hrs |
| MSLT | Level III | 0/1 (A/R) | 0/304 (PASS) |
| HTST | 150°C, 1000Hrs | 0/1 (A/R) | 0/76 (PASS) |
| TCT | -65°C ~ +150°C, @3cph, 500Cycles | 0/1 (A/R) | 0/76 (PASS) |
| PCT | 121°C, 100%R.H., 2.0atm, 168Hrs for TSOP 96Hrs for BGA | 0/1 (A/R) | 0/76 (PASS) |
| HAST | 130°C, 85%R.H., 2.3atm, 2.7V, 96Hrs | 0/1 (A/R) | 0/76 (PASS) |
| TH | 85°C, 85%R.H., 1000Hrs | 0/1 (A/R) | 0/76 (PASS) |
| ESD | HBM: R=1.5KΩ, C=100pF | ≥ ±2KV | 0/3 (PASS) |
| | MM: R=0KΩ, C=200pF | ≥ ±200V | 0/3 (PASS) |
| | CDM: Non-Socket Mode | ≥ ±1KV | 0/3 (PASS) |
| Latch-Up | Vtr(+) ≥ 1.5 * Vcc Vtr(-) ≤ -0.5 * Vcc Itr(+) ≥ 100mA Itr(-) ≤ -100mA | | 0/6 (PASS) |

Moisture Sensitivity Level Test Flow & Condition:

Electrical Test → SAT → TC (-65°C~+150°C, 5Cycles) → Bake (125°C, 24Hrs)
 → Soak Level III (30°C, 60%R.H., 192Hrs) → Convection Reflow (260 +5/-0°C,
 0~20Secs, 3Cycles) → Electrical Test → SAT

1. INTRODUCTION

In order to meet the most stringent market demands for high quality and reliability semiconductor components, Alliance maintains a strict reliability program in all products. The purpose of this report is to give an overview of the reliability status of AS4C32M16D1-5BCN. Accelerated tests are performed on product, and then the results are extrapolated to standard operating conditions in order to calculate and estimate the component's failure rate.

2. PRODUCT INFORMATION

The AS4C32M16D1-5BCN is a 32M*16 bits high-speed CMOS Double Data Rate Synchronous Dynamic Random Access Memory (DDR SDRAM) operating from a single 2.3 to 2.7 Volt power supply. By employing some new CMOS circuit design technologies and the advanced DRAM process technologies, the AS4C32M16D1-5BCN is well suited for applications requiring high memory bandwidth and particularly well suited to high performance PC applications. The AS4C32M16D1-5BCN is packaged in a standard 66pin, plastic 400mil TSOPII or a standard 60ball, plastic 8x13mm FBGA.

3. RELIABILITY

Many stress tests have been standardized in such documents as MIL-STD-883, EIAJ-IC-121, EIA/JESD22 and JEDEC-NOTE-17. From these standards, Alliance has selected a series of tests to ensure that reliability targets are being met. These tests, including life test, environmental test, ESD test and latch-up test, are discussed in the following sections.

3.1. Sample Preparation Flow

CP → Assembly 66L TSOP or 60B BGA → FT → Sampling Good Parts for Reliability Test

3.2. Life Test

The purpose of the Early Failure Rate (EFR) is to estimate the infant mortality failure rate that occurs within the first year of normal device operation by accelerating infant mortality failure mechanisms. The oven temperature for the EFR test is 125°C. Testing is performed with dynamic signals applied to the device, and the voltage is 1.2*Vint.

The purpose of the Operating Life Test (OLT) is to determine the reliability of products by accelerating thermally activated failure mechanisms by subjecting samples to extreme temperatures under biased operating condition of 1.1*Vint. The test is used to predict long-term failure rates in terms of FITs (failures in time), with one FIT representing one failure in 10⁹ device-hours. The test samples are screened directly after final electrical testing. The oven temperature for the OLT is 125°C. Testing is performed with dynamic signals applied to the device, and the voltage is 1.1*Vint.

3.2.1. Test Flow

(1) EFR Test Flow

B/I 12Hrs (125°C, 1.2*Vint) → Electrical Test (70°C & 0°C)

(2) OLT Test Flow

B/I 168Hrs (125°C, 1.1*Vint) → Electrical Test (70°C & 0°C)

→ B/I 500Hrs (125°C, 1.1*Vint) → Electrical Test (70°C & 0°C)

→ B/I 1000Hrs (125°C, 1.1*Vint) → Electrical Test (70°C & 0°C)

3.2.2. Test Criteria

| Test Item | Reference Standard | Test Condition | Prediction Duration | Pass Criteria |
|-------------|--------------------|----------------------------|---------------------|---------------|
| EFR 12Hrs | JESD22-A108 | Vcc= 1.2*Vint Ta= 125°C | 0 – 1 (Year) | ≤ 1000 (DPM) |
| OLT 1000Hrs | | Vcc= 1.1*Vint Ta= 125°C | 1 – 10 (Year) | ≤ 50 (FIT) |

3.2.3. Failure Rate Calculation and Test Result

The life test is performed for the purpose of accelerating the probable electrical and physical weakness of devices subjected to the specified conditions over an extended time period.

By choosing the appropriate thermal activation energy (E_a), data taken at an elevated temperature can be translated to a lower standard operating temperature through the Arrhenius equation:

$$T(AF) = \text{Exp} [(E_a/k) * (1/T_n - 1/T_s)] \dots (1)$$

where

$T(AF)$ = Temperature Acceleration Factor

T_n = Normal Temperature in Absolute Temperature (K)

T_s = Stress Temperature in Absolute Temperature (K)

k = Boltzmann's Constant ($8.62 * 10^{-5}$ eV/K)

E_a = Thermal Activation Energy

By choosing the appropriate electrical field acceleration rate constant (V_f), data taken at an elevated voltage can be translated to a lower standard operating voltage through the Eyring model:

$$E(AF) = \text{Exp} [V_f * (V_s - V_n)] \dots (2)$$

where

$E(AF)$ = Electrical Field Acceleration Factor

V_n = Normal Operating Voltage

V_s = Stress Operating Voltage

V_f = Electrical Field Acceleration Rate Constant

By combining the equation (1) & (2), the failure rate (λ) can be calculated by using the following equation:

$$\lambda (FIT) = [(Lamda \text{ of } 60\% \text{ CL}) / (2 * TDH * AF)] * 10^9 \dots (3)$$

where

λ = Failure Rate in FIT

AF= Acceleration Factor

$$= T(AF) * E(AF)$$

TDH= Total Device-Hours of the Test

$$= \text{Device No.} * \text{Hour}$$

Lamda CL= 60% Confidence Level (Refer to the Following Table)

| DF | Lamda |
|----|-------|
| 1 | 0.70 |
| 2 | 1.83 |
| 3 | 2.95 |
| 4 | 4.04 |
| 5 | 5.13 |
| 6 | 6.21 |
| 7 | 7.28 |
| 8 | 8.35 |
| 9 | 9.41 |
| 10 | 10.50 |

$$DF = 2 * (\text{Failure No.} + 1)$$

Therefore, from equation (3), we can get the FIT number for our OLT experiment. The MTBF can be also calculated from the reciprocal of the FIT rate multiplied by 10^9 .

3.2.3.1. EFR Test Result

A summary of Early Failure Rate (EFR) data for the AS4C32M16D1-5BCN is listed in Table 1, where the total of 1,000 devices at 125°C has been collected with 0 failure.

| Test Item | Sample | Test Result (Failure / Sample Size) | Failure Mode |
|-----------|--------|-------------------------------------|--------------|
| | | 12 Hrs | |
| EFR | 1000ea | 0/1000 [= 0 DPM] | N/A |

Table 1. EFR Test Result for 0-1 Year Prediction

3.2.3.2. OLT Test Result

A summary of Operating Life Test (OLT) data for the AS4C32M16D1-5BCN is listed in Table 2, where the total of 231,000 device-hours at 125°C has been collected with 0 failure. We then use $E_a = 0.5\text{eV}$ and $V_f = 7.0(1/V)$ (a worse case value from Alliance's foundry) to calculate the failure rate with a 60% confidence level. Table 3 shows the final result that the failure rate of 11 FIT at $T_a = 55^\circ\text{C}$ and $V_{cc} = 2.5\text{V}$ is predicted.

| Test Item | Sample | Test Result (Failure / Sample Size) | | | Failure Mode |
|-----------|--------|-------------------------------------|---------|----------|--------------|
| | | 168 Hrs | 500 Hrs | 1000 Hrs | |
| OLT | 231ea | 0/231 | 0/231 | 0/231 | N/A |

Table 2. OLT Test Result

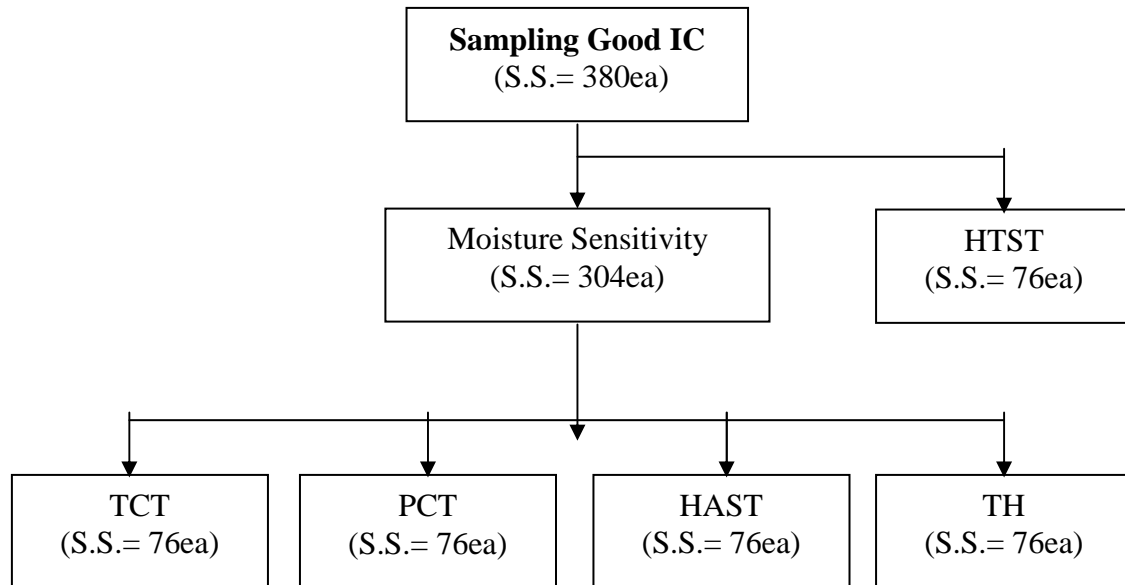
| Sample | Device | Total | Failure Rate Prediction ($E_a = 0.5\text{eV}$, $V_f = 7.0(1/V)$) | | |
|--------|---------|---------|--|--------------------|------------------|
| | -Hours | Failure | 55°C & 2.5V (% / 1000hrs) | λ (FIT) | MTBF (Hr) |
| 231ea | 231,000 | 0ea | 0.0011 | 11 | 91×10^6 |

Table 3. OLT for 1-10 Year Failure Rate Prediction

3.3. Environmental Test

The purpose of environmental test is to evaluate the ability of semiconductor device to withstand the temperature stress, humidity stress, electrical stress or any combination of these. It can reveal not only the package quality issue but also the possible error in wafer process or chip design interacting with the assembly process.

3.3.1. Test Flow



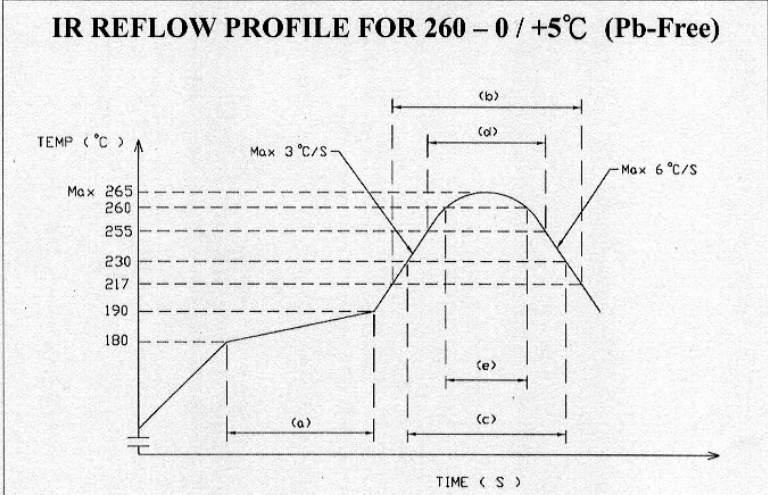
3.3.2. Test Condition and Time

3.3.2.1. Moisture Sensitivity Test

The purpose of moisture sensitivity test is to identify the classification level of nonhermetic solid state Surface Mount Devices (SMDs) that are sensitive to moisture-induced stress so that they can be properly packaged, stored, and handled to avoid subsequent thermal and mechanical damage during the assembly solder reflow attachment and/or repair operation.

*Moisture Sensitivity Test Flow

Electrical Test → SAT → TC (-65°C~+150°C, 5Cycles) → Bake (125°C, 24Hrs) → Soak Level III (30°C, 60%R.H., 192Hrs) → Convection Reflow (260 +5/-0°C, 0~20Secs, 3Cycles) → Electrical Test → SAT

| Test Item | Test Condition (Level III) | Test Time |
|-----------------------------|---|-----------|
| Temp. Cycle | -65°C ~ +150°C | 5Cycles |
| Bake | 125°C | 24Hrs |
| Unbiased Temp-Humidity Soak | 30°C, 60%R.H. | 192Hrs |
| Convection Reflow | <p style="text-align: center;">IR REFLOW PROFILE FOR 260 – 0 / +5°C (Pb-Free)</p>  <p>(a) Preheat Temp. = 60~120 seconds Max. (b) Temp. maintained above 217°C = 60~150 seconds (c) Temp. maintained above 230°C = 30~60 seconds (d) Temp. maintained above 255°C = 20~40 seconds (e) Peak Temp. Range = 260(-0/+5)°C & Max. 20 seconds P.S. Time 25°C to Peak Temp. = 8 minutes Max.</p> | 3Cycles |

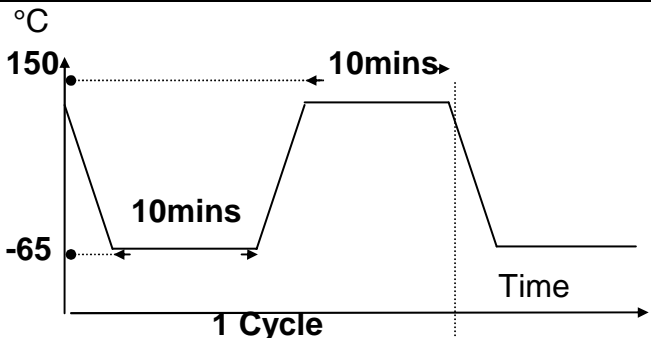
3.3.2.2. High-Temperature Storage Life Test

The high-temperature storage life test measures device resistance to a high-temperature environment that simulates a storage environment. The stress temperature is set to 150°C in order to accelerate the effect of temperature on the test samples. In the test, no voltage bias is applied to the devices.

| Test Item | Test Condition | Test Time |
|-----------|----------------|-----------|
| HTST | 150°C | 1000Hrs |

3.3.2.3. Temperature Cycling Test

The purpose of temperature cycling test is to study the effect of thermal expansion mismatch among the different components within a specific die and package system. The cycling test system has a cold dwell at -65°C and a hot dwell 150°C , and it employs a circulating air environment to ensure rapid stabilization at a specified temperature. During temperature cycling test, devices are inserted into the cycling test system and held at cold dwell for 10 minutes, then the devices are heated to hot dwell for 10 minutes. One cycle includes the duration at both extreme temperatures and the two transition times. The transition period is less than one minute at 25°C . Samples of surface mount devices must first undergo preconditioning and pass a final electrical test prior to the temperature cycling test.

| Test Item | Test Condition | Test Time |
|-----------|--|-----------|
| TCT |  <p>The graph shows a temperature profile over time. The vertical axis is labeled $^{\circ}\text{C}$ and has markers for 150 and -65. The horizontal axis is labeled Time. The profile starts at 150°C, drops to -65°C, dwells at -65°C for 10 minutes, rises to 150°C, dwells at 150°C for 10 minutes, and then returns to -65°C. A bracket labeled '1 Cycle' spans the entire duration of one such cycle.</p> | 500Cycles |

3.3.2.4. Pressure Cooker Test

The pressure cooker test is an environmental test that measures device resistance to moisture penetration and the effect of galvanic corrosion. The stress conditions for the pressure cooker are 121°C , 100% relative humidity, and 2.0atm pressure. Samples of surface mount devices are subjected to preconditioning and a final electrical test prior to the pressure cooker test.

| Test Item | Test Condition | Test Time |
|-----------|-------------------------|----------------------------------|
| PCT | 121°C, 100%R.H., 2.0atm | 168Hrs for TSOP 96Hrs for BGA |

3.3.2.5. Highly-Accelerated Temperature and Humidity Stress Test

The highly-accelerated temperature and humidity stress test is performed for the purpose of evaluating the reliability of nonhermetic packaged solid-state device in an environment with high humidity. It employs severe condition of temperature, humidity, and bias that accelerate the penetration of moisture through the external protective material (encapsulant or seal) or along the interface between the external protective material and the metallic conductor that pass through it. The stress conditions of the HAST are 130°C, 85% relativity humidity, 2.3atm pressure, and 2.7V maximum operating voltage. Samples of surface mount devices are subjected to preconditioning and a final electrical test prior to the highly-accelerated temperature and humidity stress test.

| Test Item | Test Condition | Test Time |
|-----------|------------------------------|-----------|
| HAST | 130°C, 85%R.H., 2.3atm, 2.7V | 96Hrs |

3.3.2.6. Steady State Temperature and Humidity Life Test

The temperature and humidity test is an environmental test designed to measure the corrosion and moisture resistance of plastic-encapsulated circuits. The stress conditions of the TH are 85°C and 85% relativity humidity. Samples of surface mount devices are subjected to preconditioning and a final electrical test prior to the steady state temperature and humidity life test.

| Test Item | Test Condition | Test Time |
|-----------|----------------|-----------|
| TH | 85°C, 85%R.H. | 1000Hrs |

3.3.3. Test Criteria and Result

Table 4 shows the test results and reference standard of environmental test. The test status and results of AS4C32M16D1-5BCN are also presented in the table. All pass from these test results mean that Alliance's SDRAM products are much more durable in most of their service environment.

| Test Item | Reference Standard | A/R Criteria | Failure/S.S. | Status | Failure Mode |
|----------------------|--------------------|--------------|--------------|--------|--------------|
| Moisture Sensitivity | J-STD-020 | 0/1 | 0/304 | PASS | N/A |
| HTST | JESD22-A103 | 0/1 | 0/76 | PASS | N/A |
| TCT* | JESD22-A104 | 0/1 | 0/76 | PASS | N/A |
| PCT* | JESD22-A102 | 0/1 | 0/76 | PASS | N/A |
| HAST* | JESD22-A110 | 0/1 | 0/76 | PASS | N/A |
| TH* | JESD22-A101 | 0/1 | 0/76 | PASS | N/A |

* Sampling from Moisture Sensitivity

Table 4. Environmental Test Criteria and Result

3.4. ESD Test

Electrical discharge into semiconductor product is one of the leading causes of device failure in the customer's manufacturing process. Alliance performs the ESD test to ensure that the performance of AS4C32M16D1-5BCN will not be degraded to an unacceptable level by exposure to a succession of electrostatic discharge. The test methods and test results are shown in Table 5.

| Test Item | Test Method | | | | Result (F/S.S) |
|-----------|--------------------|------------------|----------|--------|----------------|
| | Reference Standard | Test Condition | Criteria | Sample | |
| H.B.M. | JESD22-A114 | R=1.5KΩ, C=100pF | ≥±2KV | 3ea | 0/3 |
| M.M. | JESD22-A115 | R=0KΩ, C=200pF | ≥±200V | 3ea | 0/3 |
| C.D.M. | JESD22-C101 | Non-Socket Mode | ≥±1KV | 3ea | 0/3 |

Table 5. ESD Test Condition and Result

3.5. Latch-Up Test

CMOS products can be prone to over-voltage exceeding the maximum device rating if the parasitic p-n-p-n SCRs (Silicon-controlled rectifier) are improperly biased. When the SCR turns on, it draws excessive current and causes products being damaged by thermal runaway. The Table 6 shows the latch-up test method and the test result of no failure.

| Test Item | Test Method | | | Result (F/S.S) |
|-----------|--------------------|--|--------|----------------|
| | Reference Standard | Test Condition & Criteria | Sample | |
| Latch-Up | JESD78 | $V_{tr(+)} \geq 1.5 * V_{cc}$ $V_{tr(-)} \leq -0.5 * V_{cc}$ $I_{tr(+)} \geq 100mA$ $I_{tr(-)} \leq -100mA$ | 6ea | 0/6 |

Table 6. Latch-Up test Condition and Result

4. CONCLUSION

Reliability test is to ensure the ability of a product in order to perform a required function under specific conditions for a certain period of time. Through those tests, the devices of potential failure can be screened out before shipping to the customer. At the same time, the test results are fed back to process, design and other related departments for improving product quality and reliability.

According to the life time test data, *the short-term 12Hrs failure rate (= the normal operation 0-1 year) of AS4C32M16D1-5BCN is equal to 0 DPM at Ta=55°C and Vcc=2.5V with 60% confidence level AND the long-term 1000Hrs failure rate (= the normal operation 1-10 year) of AS4C32M16D1-5BCN is equal to 11 FIT at Ta=55°C and Vcc=2.5V with 60% confidence level.* The results of environmental test, ESD test and latch-up test also ensure that the AS4C32M16D1-5BCN is manufactured under a precise control of quality work by Alliance and its subcontractors. ***Thus, this experiment based on the Alliance reliability test standard for above test items can all pass.***

With the extensive research and development activities and the cooperation of all departments, Alliance continuously sets and maintains higher standard of quality and reliability to satisfy the future demand of its customers.